

## **isc** Silicon NPN Power Transistors

## TIP41

### DESCRIPTION

- DC Current Gain -h<sub>FE</sub> = 30(Min)@ I<sub>C</sub>= 0.3A
- Collector-Emitter Sustaining Voltage-
- : V<sub>CEO(SUS)</sub> = 40V(Min)
- Complement to Type TIP42
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

Designed for use in general purpose amplifer and switching applications

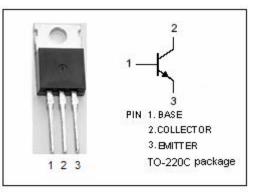
ABSOLUTE	MAXIMUM RATING	GS(T₂=25℃)
ADOOLOIL		

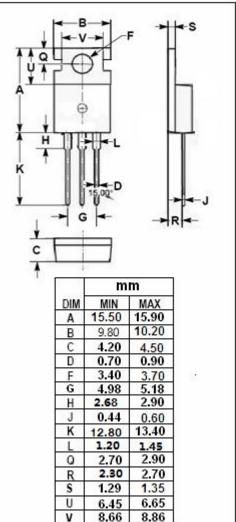
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	40	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V	
$V_{\text{EBO}}$	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	6	А	
Ісм	Collector Current-Peak	10	А	
I <sub>B</sub>	Base Current	2	А	
Pc	Collector Power Dissipation Tc=25°C	65	W	
	Collector Power Dissipation T <sub>a</sub> =25°C	2		
Tj	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.67	°C/W
Rth j-a	Thermal Resistance, Junction to Ambient	57	°C/W

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## ELECTRICAL CHARACTERISTICS

### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>CEO</sub> (SUS)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	40		V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 0.6A		1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 6A; V <sub>CE</sub> = 4V		2.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0		0.4	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 40V; I <sub>B</sub> = 0		0.7	mA
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.3A ; V <sub>CE</sub> = 4V	30		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A ; V <sub>CE</sub> = 4V	15	75	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 10V	3		MHz

Switching Time

t <sub>on</sub>	Turn-On Time	I <sub>C</sub> = 6A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.6A; V <sub>BE(off)</sub> = 4V, R <sub>L</sub> = 5 Ω	0.6	μ <b>S</b>
t <sub>off</sub>	Turn-Off Time		1.0	μ <b>S</b>

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